

# SANYO Semiconductors DATA SHEET

# ATP203 — General-Purpose Switching Device Applications

#### **Features**

- · Low ON-resistance.
- · Large current.
- · Slim package.
- · 4.5V drive.
- · Halogen free compliance.

### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	ID		75	А
Drain Current (PW≤10μs)	IDP	PW≤10μs, duty cycle≤1%	225	А
Allowable Power Dissipation	PD	Tc=25°C	50	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		52	mJ
Avalanche Current *2	IAV		38	А

Note :\*1 VDD=10V, L=50 $\mu$ H, IAV=38A

\*2 L≤50µH, Single pulse

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
	Syllibol		min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μА
Gate-to-Source Leakage Current	IGSS	VGS=±16V, VDS=0V			±10	μΑ

Marking: ATP203 Continued on next page.

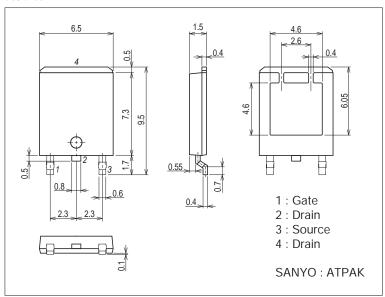
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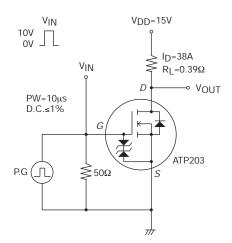
Parameter	Symbol	Conditions	Ratings			1.1
			min	typ	max	Unit
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	VDS=10V, ID=38A	13	22		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=38A, VGS=10V		6.3	8.2	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =19A, V <sub>GS</sub> =4.5V		9.5	13.5	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		2750		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		450		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		265		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		24		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		420		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		130		ns
Fall Time	tf	See specified Test Circuit.		75		ns
Total Gate Charge	Qg	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =75A		44		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =75A		14		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =75A		5.6		nC
Diode Forward Voltage	VSD	IS=75A, VGS=0V		1.02	1.2	V

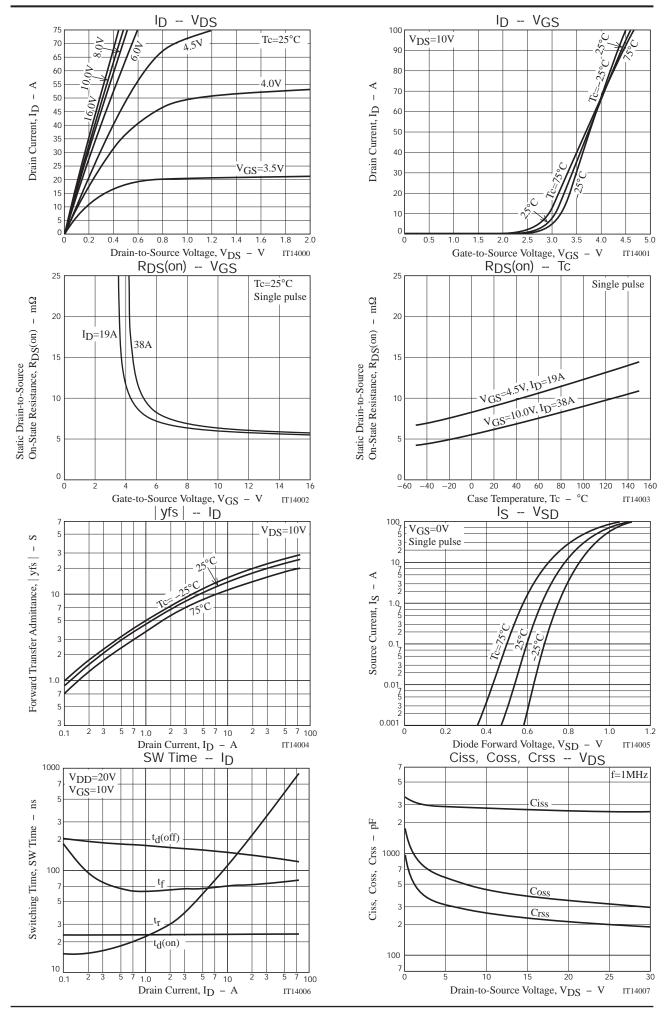
# Package Dimensions

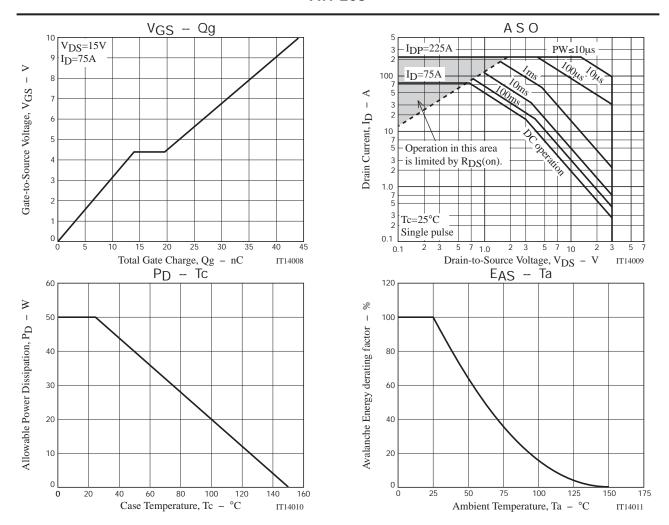
unit : mm (typ) 7057-001



## **Switching Time Test Circuit**







Note on usage: Since the ATP203 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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